

isc Silicon NPN Power Transistor

2SC3852

DESCRIPTION

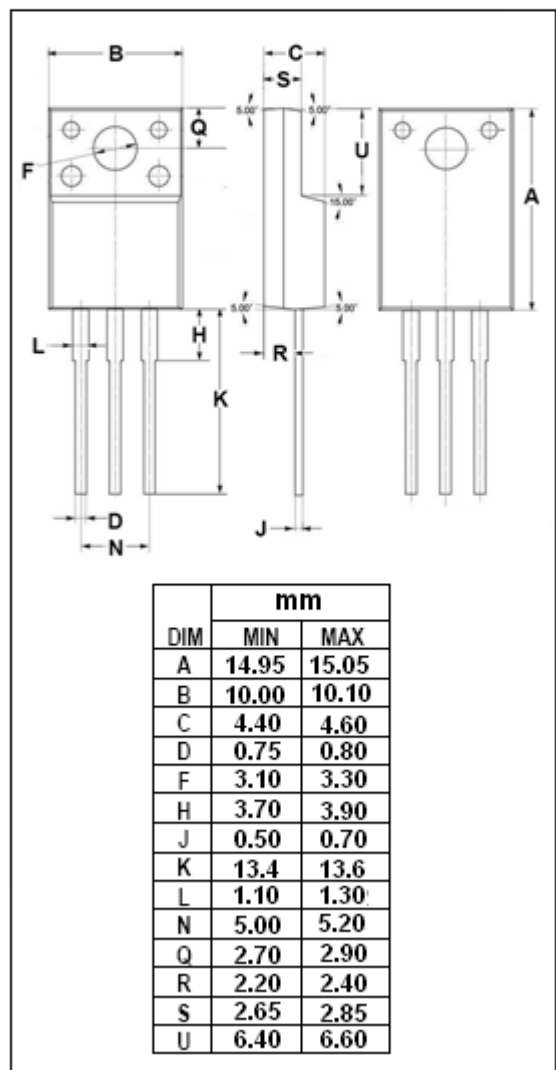
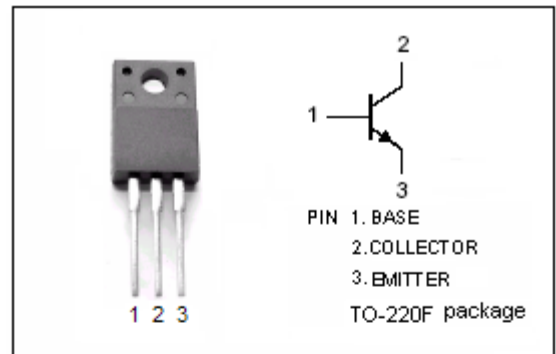
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V(\text{Min})$
- DC Current Gain-
: $h_{FE} = 200(\text{Min}) @ I_C = 0.5A$

APPLICATIONS

- Driver for solenoid and motor, series regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor

2SC3852

ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	60			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 50mA			0.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			100	μ A
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 4V	200			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		50		pF
f _T	Current-Gain—Bandwidth Product	I _E = -0.2A; V _{CE} = 12V		15		MHz

Switching Times

t _{on}	Turn-On Time	I _C = 1A; I _{B1} = 15mA; I _{B2} = -30mA; V _{CC} = 20V; R _L = 20 Ω		0.8		μ s
t _{stg}	Storage Time			3.0		μ s
t _f	Fall Time			1.2		μ s